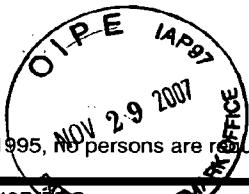


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Application Number	-Unassigned 10590485
Filing Date	04/02/08
First Named Inventor	Igor BARGATIN et al.
Group Art Unit	Unassigned 2855
Examiner Name	Unassigned M. Noori

Attorney Docket Number 049411-0340

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
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	A2	2002/0175408	A1	MAJUMDAR et al.	11/28/2002	
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/MN/	A30	WO	2003/095616	A2	California Inst. of Tech.	11/20/2003		
/MN/	A31	WO	2003/095617	A2	California Inst. of Tech.	11/20/2003		
/MN/	A32	WO	2004/041998	A2	California Inst. of Tech.	05/21/2004		

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2 of 3

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First Named Inventor	Igor BARGATIN et al.
Group Art Unit	Unassigned 2855
Examiner Name	Unassigned M. Noori

Attorney Docket Number

049411-0340

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
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<p style="text-align: center;">Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT Filed: <u>November 29, 2007</u> (use as many sheets as necessary)</p>				Complete if Known	
Sheet	3	of	3	Application Number	Unassigned 10590485
				Filing Date	04/02/08
				First Named Inventor	Igor BARGATIN et al.
				Group Art Unit	Unassigned 2855
				Examiner Name	Unassigned M. Noori
				Attorney Docket Number	049411-0340

NON PATENT LITERATURE DOCUMENTS

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